

# SILICON POWER TRANSISTOR 2SA1647, 2SA1647-Z

### PNP SILICON EPITAXIAL TRANSISTOR FOR HIGH-SPEED SWITCHING

The 2SA1647 is a mold power transistor developed for high-speed switching and features a very low collector-to-emitter saturation voltage.

This transistor is ideal for use in switching regulators, DC/DC converters, motor drivers, solenoid drivers, and other low-voltage power supply devices, as well as for high-current switching.

#### FEATURES

- Available for high-current control in small dimension
- Z type is a lead processed product and is deal for mounting a hybrid IC.
- Low collector saturation voltage:  
 $V_{CE(sat)} = -0.3 \text{ V MAX. (@ } I_c = -3 \text{ A)}$
- Fast switching speed:  
 $t_f = 0.4 \mu\text{s MAX. (@ } I_c = -3 \text{ A)}$
- High DC current gain and excellent linearity

#### ABSOLUTE MAXIMUM RATINGS ( $T_A = 25^\circ\text{C}$ )

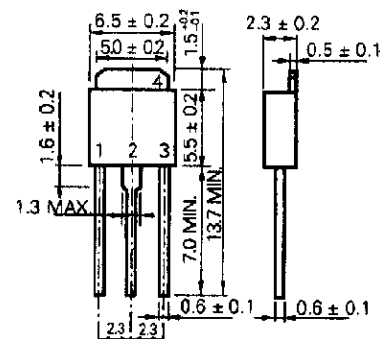
Parameter	Symbol	Ratings	Unit
Collector to base voltage	$V_{CBO}$	-150	V
Collector to emitter voltage	$V_{CEO}$	-100	V
Base to emitter voltage	$V_{EBO}$	-7.0	V
Collector current (DC)	$I_{C(DC)}$	-5.0	A
Collector current (pulse)	$I_{C(pulse)^*}$	-10	A
Base current (DC)	$I_{B(DC)}$	-2.5	A
Total power dissipation	$P_T (T_c = 25^\circ\text{C})$	18	W
Total power dissipation	$P_T (T_A = 25^\circ\text{C})$	1.0**, 2.0***	W
Junction temperature	$T_j$	150	$^\circ\text{C}$
Storage temperature	$T_{stg}$	-55 to +150	$^\circ\text{C}$

\*:  $PW \leq 10 \text{ ms}$ , duty cycle  $\leq 50\%$

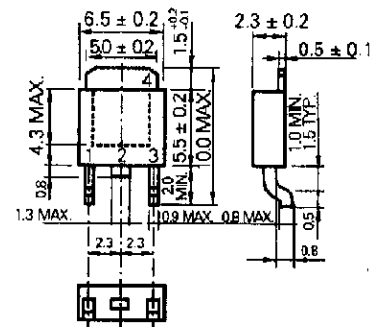
\*\* : Printing board mounted

\*\*\*:  $7.5 \text{ mm}^2 \times 0.7 \text{ mm}$  ceramic board mounted

#### PACKAGE DRAWING (UNIT: mm)



TO-251 (MP-3)



TO-252 (MP-3Z)

Electrode Connection  
1. Base  
2. Collector  
3. Emitter

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**ELECTRICAL CHARACTERISTICS (T<sub>A</sub> = 25°C)**

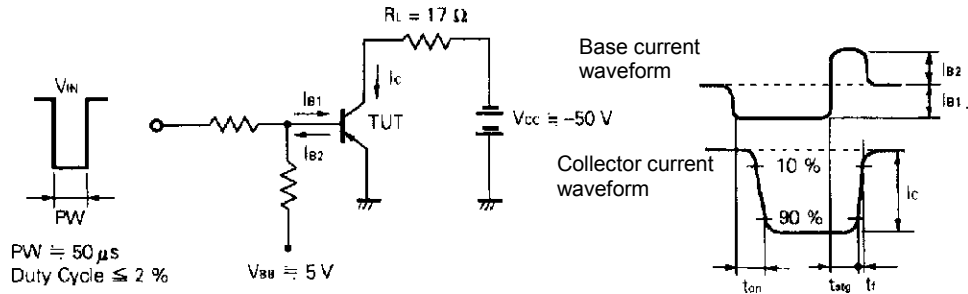
Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Collector to emitter voltage	V <sub>CEO(SUS)</sub>	I <sub>C</sub> = -2.5 A, I <sub>B</sub> = -0.25 A, L = 1 mH	-100			V
Collector to emitter voltage	V <sub>CEX(SUS)</sub>	I <sub>C</sub> = -2.5 A, I <sub>B1</sub> = -I <sub>B2</sub> = -0.25 A, V <sub>BE(OFF)</sub> = 1.5 V, L = 180 μH, clamped	-100			V
Collector cutoff current	I <sub>CBO</sub>	V <sub>CB</sub> = -100 V, I <sub>E</sub> = 0			-10	μA
Collector cutoff current	I <sub>CER</sub>	V <sub>CE</sub> = -100 V, R <sub>BE</sub> = 50 Ω, T <sub>A</sub> = 125 °C			-1.0	mA
Collector cutoff current	I <sub>CEX1</sub>	V <sub>CE</sub> = -100 V, V <sub>BE(OFF)</sub> = 1.5 V			-10	μA
Collector cutoff current	I <sub>CEX2</sub>	V <sub>CE</sub> = -100 V, V <sub>BE(OFF)</sub> = 1.5 V, T <sub>A</sub> = 125 °C			-1.0	mA
Emitter cutoff current	I <sub>EBO</sub>	V <sub>EB(OFF)</sub> = -5.0 V, I <sub>C</sub> = 0			-10	μA
DC current gain	h <sub>FE1</sub> *	V <sub>CE</sub> = -2.0 V, I <sub>C</sub> = -0.5 A	100			
DC current gain	h <sub>FE2</sub> *	V <sub>CE</sub> = -2.0 V, I <sub>C</sub> = -1.0 A	100		400	
DC current gain	h <sub>FE3</sub> *	V <sub>CE</sub> = -2.0 V, I <sub>C</sub> = -3.0 A	60			
Collector saturation voltage	V <sub>CE(sat)1</sub> *	I <sub>C</sub> = -3.0 A, I <sub>B</sub> = -0.15 A			-0.3	V
Collector saturation voltage	V <sub>CE(sat)2</sub> *	I <sub>C</sub> = -4.0 A, I <sub>B</sub> = -0.2 A			-0.5	V
Base saturation voltage	V <sub>BE(sat)1</sub> *	I <sub>C</sub> = -3.0 A, I <sub>B</sub> = -0.15 A			-1.2	V
Base saturation voltage	V <sub>BE(sat)2</sub> *	I <sub>C</sub> = -4.0 A, I <sub>B</sub> = -0.2 A			-1.5	V
Collector capacitance	C <sub>ob</sub>	V <sub>CB</sub> = -10 V, I <sub>E</sub> = 0, f = 1.0 MHz		110		pF
Gain bandwidth product	f <sub>T</sub>	V <sub>CE</sub> = -10 V, I <sub>C</sub> = 0.5 A		90		MHz
Turn-on time	t <sub>on</sub>	I <sub>C</sub> = -3.0 A, R <sub>L</sub> = 17 Ω, I <sub>B1</sub> = -I <sub>B2</sub> = -0.15 A, V <sub>CC</sub> ≐ -50 V Refer to the test circuit.			0.3	μs
Storage time	t <sub>stg</sub>				1.5	μs
Fall time	t <sub>f</sub>				0.4	μs

\* Pulse test PW ≤ 350 μs, duty cycle ≤ 2%/Pulsed

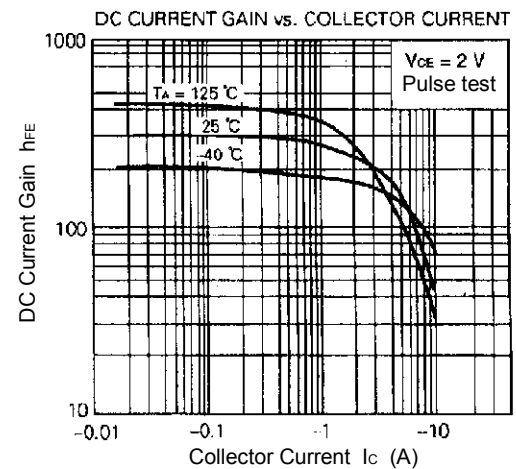
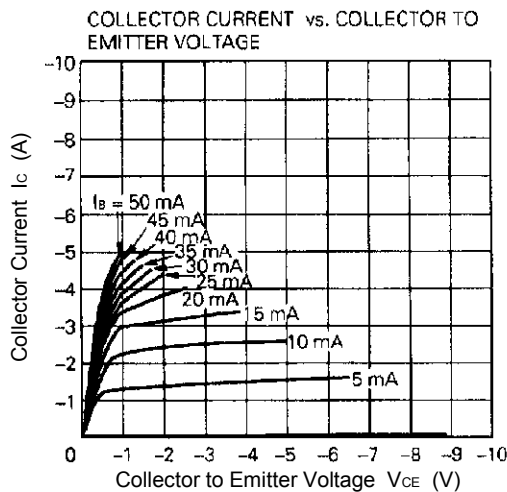
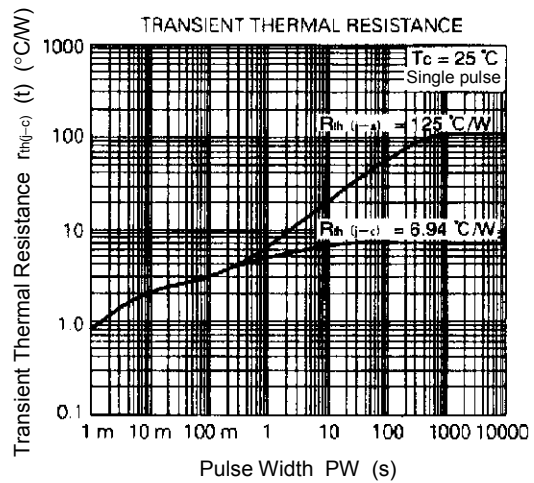
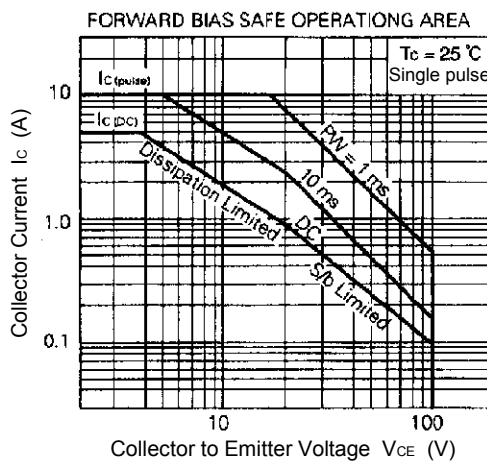
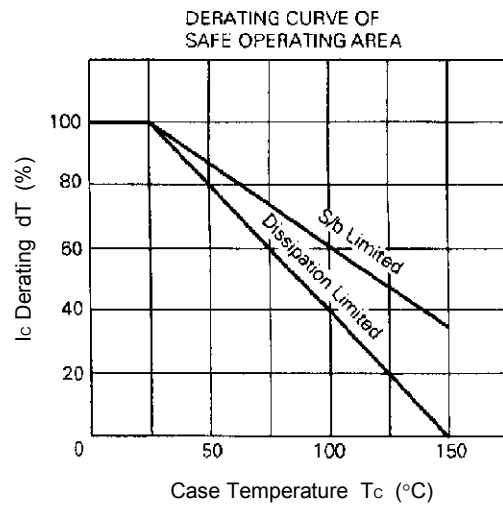
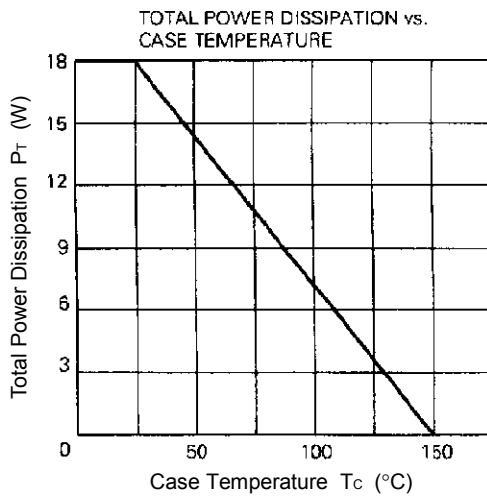
**h<sub>FE</sub> CLASSIFICATION**

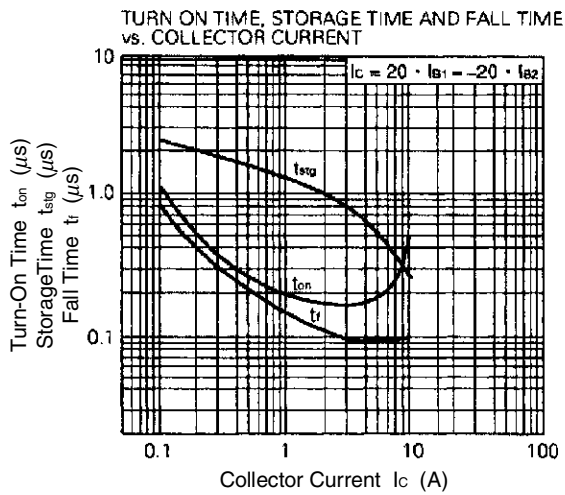
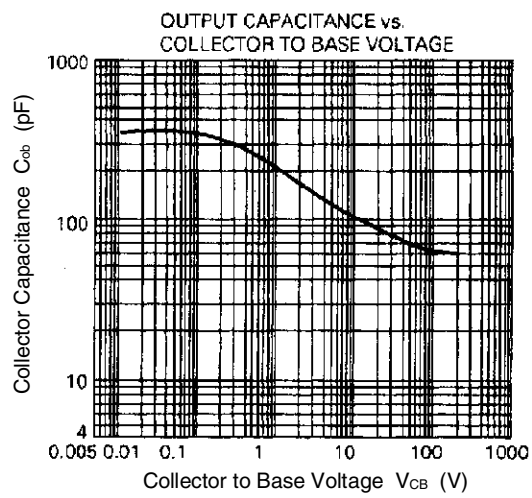
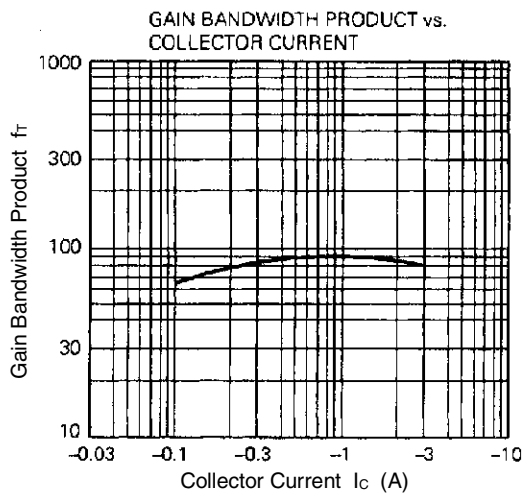
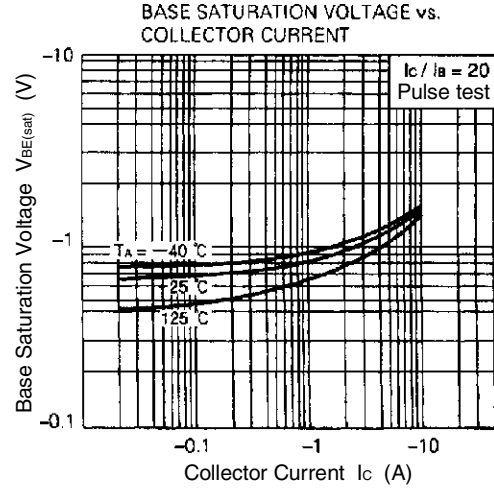
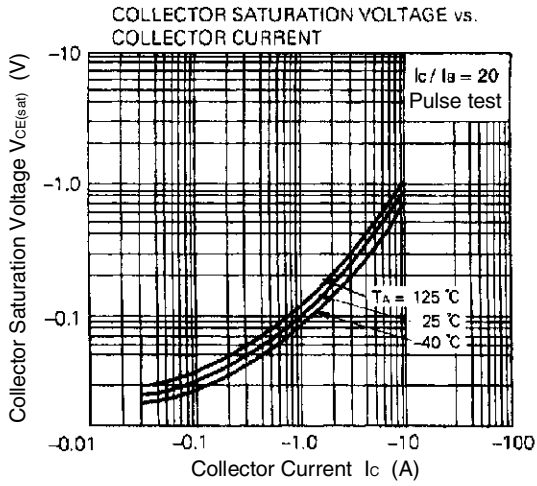
Marking	M	L	K
h <sub>FE2</sub>	100 to 200	150 to 300	200 to 400

**SWITCHING TIME TEST CIRCUIT**



TYPICAL CHARACTERISTICS (T<sub>A</sub> = 25°C)





[MEMO]

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